

### Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

### Listing of Claims

1-18. (Canceled)

19. (Currently amended) A method for manufacturing a light-emitting device, comprising:

- forming a thin film transistor over a substrate;
- forming a first insulating film over the thin film transistor;
- hardening a top surface of the first insulating film by performing a first plasma treatment on the first insulating film after forming the first insulating film;
- forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;
- forming a second insulating film over the first insulating film and an edge portion of the first electrode;
- hardening a top surface of the second insulating film by performing a second plasma treatment at least on the second insulating film after forming the second insulating film;
- forming a polymer film on the first electrode and the second insulating film;
- forming a low molecular weight film on the polymer film; and
- forming a second electrode on the low molecular weight film.

20. (Previously Presented) A method according to claim 1, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

21. (Previously Presented) A method according to claim 1, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

22. (Currently amended) A method for manufacturing a light-emitting device, comprising:

- forming a thin film transistor over a substrate;
  - forming a first insulating film over the thin film transistor;
  - hardening a top surface of the first insulating film by performing a first plasma treatment on the first insulating film after forming the first insulating film;
  - forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;
  - forming a second insulating film over the first insulating film and an edge portion of the first electrode;
  - hardening a top surface of the second insulating film by performing a second plasma treatment at least on the second insulating film after forming the second insulating film;
  - forming a polymer film on the first electrode and the second insulating film;
  - forming a low molecular weight film on the polymer film; and
  - forming a second electrode on the low molecular weight film,
- wherein ~~upper surfaces of the first and second insulating films are hardened by performing the first and second plasma treatments~~ resin films.

23. (Previously Presented) A method according to claim 22, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

24. (Previously Presented) A method according to claim 22, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video

camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

25. (Currently amended) A method for manufacturing a light-emitting device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

hardening a top surface of the first insulating film by performing a plasma treatment on the first insulating film after forming the first insulating film;

forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;

forming a second insulating film over the first insulating film and an edge portion of the first electrode;

forming a diamond-like carbon film over the second insulating film;

forming a polymer film on the first electrode and the diamond-like carbon film;

forming a low molecular weight film on the polymer film; and

forming a second electrode on the low molecular weight film .

26. (Previously Presented) A method according to claim 25, wherein the polymer film is a luminescent layer and the low molecular weight film is an electron transport layer or an electron injection layer.

27. (Previously Presented) A method according to claim 25, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.

28. (Currently amended) A method for manufacturing a light-emitting device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;  
hardening a top surface of the first insulating film by performing a plasma treatment on  
the first insulating film after forming the first insulating film;  
forming a first electrode over the first insulating film, wherein the first electrode is  
electrically connected to the thin film transistor;  
forming a second insulating film over the first insulating film and an edge portion of the  
first electrode;  
forming a diamond-like carbon film on the second insulating film;  
forming a polymer film on the first electrode and the diamond-like carbon film;  
forming a low molecular weight film on the polymer film; and  
forming a second electrode on the low molecular weight film;  
~~wherein an upper surface of the first and second insulating film is hardened by~~  
~~performing the plasma treatment. films are resin films.~~

29. (Previously Presented) A method according to claim 28, wherein the polymer film is  
a luminescent layer and the low molecular weight film is an electron transport layer or an  
electron injection layer.

30. (Previously Presented) A method according to claim 28, wherein the light emitting  
device is incorporated into an electronic device selected from the group consisting of a video  
camera, a digital camera, a goggle type display, a navigation system, a personal computer, a  
portable information terminal.

31-33 (Canceled)

34. (New) A method for manufacturing a light-emitting device, comprising:  
forming a thin film transistor over a substrate;  
forming a first insulating film over the thin film transistor;  
hardening a top surface of the first insulating film by performing a first plasma treatment  
on the first insulating film after forming the first insulating film;

forming a first electrode over the first insulating film, wherein the first electrode is electrically connected to the thin film transistor;

forming a second insulating film over the first insulating film and an edge portion of the first electrode; and

hardening a top surface of the second insulating film by performing a second plasma treatment at least on the second insulating film after forming the second insulating film,

wherein the first and second insulating films are resin films.

35. (New) A method according to claim 34, wherein a polymer film is formed on the first electrode and the second insulating film, a low molecular weight film is formed on the polymer film; and a second electrode is formed on the low molecular weight film.

36. (New) A method according to claim 34, wherein the light emitting device is incorporated into an electronic device selected from the group consisting of a video camera, a digital camera, a goggle type display, a navigation system, a personal computer, a portable information terminal.